

# Hideto Miyake

## List of Publications by Year in descending order

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267  
papers

4,935  
citations

136950

32  
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138484

58  
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270  
all docs

270  
docs citations

270  
times ranked

2755  
citing authors

#	ARTICLE	IF	CITATIONS
1	Fabrication and characterization of low defect density GaN using facet-controlled epitaxial lateral overgrowth (FACELO). Journal of Crystal Growth, 2000, 221, 316-326.	1.5	396
2	Recent Progress in Selective Area Growth and Epitaxial Lateral Overgrowth of III-Nitrides: Effects of Reactor Pressure in MOVPE Growth. Physica Status Solidi A, 1999, 176, 535-543.	1.7	251
3	Preparation of high-quality AlN on sapphire by high-temperature face-to-face annealing. Journal of Crystal Growth, 2016, 456, 155-159.	1.5	231
4	AlGaN-based deep UV LEDs grown on sputtered and high temperature annealed AlN/sapphire. Applied Physics Letters, 2018, 112, .	3.3	171
5	Annealing of an AlN buffer layer in N <sub>2</sub> /CO for growth of a high-quality AlN film on sapphire. Applied Physics Express, 2016, 9, 025501.	2.4	166
6	Effects of sodium on electrical properties in Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystal. Applied Physics Letters, 2014, 104, .	3.3	113
7	Impacts of Si-doping and resultant cation vacancy formation on the luminescence dynamics for the near-band-edge emission of Al <sub>0.6</sub> Ga <sub>0.4</sub> N films grown on AlN templates by metalorganic vapor phase epitaxy. Journal of Applied Physics, 2013, 113, .	2.5	98
8	Effects of Reactor Pressure on Epitaxial Lateral Overgrowth of GaN via Low-Pressure Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 1999, 38, L1000-L1002.	1.5	95
9	Improvement mechanism of sputtered AlN films by high-temperature annealing. Journal of Crystal Growth, 2018, 502, 41-44.	1.5	76
10	Optical constants of CuGaSe <sub>2</sub> and CuInSe <sub>2</sub> . Journal of Applied Physics, 1998, 84, 5202-5209.	2.5	75
11	Sharp band edge photoluminescence of high-purity CuInS <sub>2</sub> single crystals. Applied Physics Letters, 2001, 78, 742-744.	3.3	75
12	Room-temperature operation of AlGaN ultraviolet-B laser diode at 298 nm on lattice-relaxed Al <sub>0.6</sub> Ga <sub>0.4</sub> N/AlN/sapphire. Applied Physics Express, 2020, 13, 031004.	2.4	72
13	Preparation of Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystals from Sn solutions. Journal of Crystal Growth, 2012, 341, 38-41.	1.5	69
14	Correlation between intrinsic defects and electrical properties in the high-quality Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystal. Applied Physics Letters, 2013, 103, .	3.3	69
15	Optical and Crystalline Properties of Epitaxial-Lateral-Overgrown-GaN Using Tungsten Mask by Hydride Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 1999, 38, L356-L359.	1.5	60
16	Formation of GaN Self-Organized Nanotips by Reactive Ion Etching. Japanese Journal of Applied Physics, 2001, 40, L1301-L1304.	1.5	59
17	Reduction of threading dislocation density and suppression of cracking in sputter-deposited AlN templates annealed at high temperatures. Applied Physics Express, 2019, 12, 065501.	2.4	59
18	Fabrication of Deep-Ultraviolet-Light-Source Tube Using Si-Doped AlGaN. Applied Physics Express, 2011, 4, 042103.	2.4	58

#	ARTICLE	IF	CITATIONS
19	Native cation vacancies in Si-doped AlGa <sub>N</sub> studied by monoenergetic positron beams. Journal of Applied Physics, 2012, 111, .	2.5	53
20	High-quality AlN epitaxial films on (0001)-faced sapphire and 6H-SiC substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2023-2026.	0.8	51
21	Impact of high-temperature annealing of AlN layer on sapphire and its thermodynamic principle. Japanese Journal of Applied Physics, 2016, 55, 05FLO2.	1.5	48
22	Low-pressure HVPE growth of crack-free thick AlN on a trench-patterned AlN template. Journal of Crystal Growth, 2009, 311, 2831-2833.	1.5	47
23	Dependence of internal quantum efficiency on doping region and Si concentration in Al-rich AlGa <sub>N</sub> quantum wells. Applied Physics Letters, 2012, 101, 042110.	3.3	45
24	High-quality and highly-transparent AlN template on annealed sputter-deposited AlN buffer layer for deep ultra-violet light-emitting diodes. AIP Advances, 2017, 7, 055110.	1.3	45
25	Suppression of dislocation-induced spiral hillocks in MOVPE-grown AlGa <sub>N</sub> on face-to-face annealed sputter-deposited AlN template. Applied Physics Letters, 2020, 116, .	3.3	44
26	Deep Ultraviolet Light Source from Ultrathin GaN/AlN MQW Structures with Output Power Over 2 Watt. Advanced Optical Materials, 2019, 7, 1801763.	7.3	43
27	Growth of Crack-Free and High-Quality AlGa <sub>N</sub> with High Al Content Using Epitaxial AlN (0001) Films on Sapphire. Physica Status Solidi A, 2002, 194, 498-501.	1.7	41
28	Growth of Cu <sub>2</sub> ZnSnSe <sub>4</sub> single crystals from Sn solutions. Journal of Crystal Growth, 2012, 354, 147-151.	1.5	41
29	Growth of Thick AlN Layer by Hydride Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2005, 44, L505-L507.	1.5	37
30	Selective Area Growth of GaN Using Tungsten Mask by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 1998, 37, L845-L848.	1.5	36
31	Ultraviolet-B band lasers fabricated on highly relaxed thick Al <sub>0.55</sub> Ga <sub>0.45</sub> N films grown on various types of AlN wafers. Japanese Journal of Applied Physics, 2019, 58, SC1052.	1.5	36
32	AlGa <sub>N</sub> -based UV-B laser diode with a high optical confinement factor. Applied Physics Letters, 2021, 118, .	3.3	36
33	Transmission Electron Microscopy Investigation of Dislocations in GaN Layer Grown by Facet-Controlled Epitaxial Lateral Overgrowth. Japanese Journal of Applied Physics, 2001, 40, L309-L312.	1.5	34
34	Internal loss of AlGa <sub>N</sub> -based ultraviolet-B band laser diodes with p-type AlGa <sub>N</sub> cladding layer using polarization doping. Applied Physics Express, 2020, 13, 071008.	2.4	34
35	Reactor-pressure dependence of growth of a-plane GaN on r-plane sapphire by MOVPE. Journal of Crystal Growth, 2008, 310, 4979-4982.	1.5	33
36	Low dislocation density AlN on sapphire prepared by double sputtering and annealing. Applied Physics Express, 2020, 13, 095501.	2.4	32

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37	Growth of High-Quality AlN and AlGa <sub>N</sub> Films on Sputtered AlN/Sapphire Templates via High-Temperature Annealing. <i>Physica Status Solidi (B): Basic Research</i> , 2018, 255, 1700506.	1.5	30
38	Growth and Characterization of AlGa <sub>N</sub> Multiple Quantum Wells for Electron-Beam Target for Deep-Ultraviolet Light Sources. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 01AF03.	1.5	28
39	Reduction in the concentration of cation vacancies by proper Si-doping in the well layers of high AlN mole fraction Al <sub>x</sub> Ga <sub>1-x</sub> N multiple quantum wells grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2015, 107, 121602.	3.3	27
40	Quantitative evaluation of strain relaxation in annealed sputter-deposited AlN film. <i>Journal of Crystal Growth</i> , 2019, 512, 16-19.	1.5	27
41	AlGa <sub>N</sub> Channel High Electron Mobility Transistors with Regrown Ohmic Contacts. <i>Electronics (Switzerland)</i> , 2021, 10, 635.	3.1	27
42	Growth of CuGaSe <sub>2</sub> single crystals by the traveling heater method. <i>Journal of Crystal Growth</i> , 1989, 98, 610-616.	1.5	26
43	Growth and characterization of Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystals. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013, 210, 1328-1331.	1.8	26
44	High-quality AlN/sapphire templates prepared by thermal cycle annealing for high-performance ultraviolet light-emitting diodes. <i>Applied Physics Express</i> , 2021, 14, 035505.	2.4	26
45	THM growth and properties of CuInSe <sub>2</sub> single crystals. <i>Journal of Crystal Growth</i> , 1992, 125, 548-552.	1.5	25
46	AlN homoepitaxial growth on sublimation-AlN substrate by low-pressure HVPE. <i>Journal of Crystal Growth</i> , 2012, 350, 69-71.	1.5	24
47	Annealing behaviors of vacancy-type defects in AlN deposited by radio-frequency sputtering and metalorganic vapor phase epitaxy studied using monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2020, 128, .	2.5	24
48	Photoluminescence of CuAl <sub>x</sub> Ga <sub>1-x</sub> Se <sub>2</sub> crystals grown by chemical vapor transport. <i>Journal of Applied Physics</i> , 1989, 65, 5212-5215.	2.5	23
49	Effects of initial stages on the crystal quality of nonpolar a-plane AlN on r-plane sapphire by low-pressure HVPE. <i>Journal of Crystal Growth</i> , 2009, 311, 3801-3805.	1.5	23
50	Growth of High-Quality Si-Doped AlGa <sub>N</sub> by Low-Pressure Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 095502.	1.5	23
51	Fabrication of high-crystallinity a-plane AlN films grown on r-plane sapphire substrates by modulating buffer-layer growth temperature and thermal annealing conditions. <i>Journal of Crystal Growth</i> , 2017, 468, 845-850.	1.5	23
52	Photoreflectance of CuInS <sub>2</sub> single crystal prepared by traveling heater method. <i>Journal of Physics and Chemistry of Solids</i> , 2003, 64, 2021-2024.	4.0	22
53	Influence of off-cut angle of r-plane sapphire on the crystal quality of nonpolar a-plane AlN by LP-HVPE. <i>Journal of Crystal Growth</i> , 2009, 311, 4473-4477.	1.5	22
54	Limits on Astrophysical Antineutrinos with the KamLAND Experiment. <i>Astrophysical Journal</i> , 2022, 925, 14.	4.5	22

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55	Inhomogeneous distribution of defect-related emission in Si-doped AlGaIn epitaxial layers with different Al content and Si concentration. Journal of Applied Physics, 2014, 115, .	2.5	21
56	Thermo-physical properties of Cu <sub>2</sub> ZnSnS <sub>4</sub> single crystal. Journal of Crystal Growth, 2014, 393, 167-170.	1.5	21
57	Growth of CuGaS <sub>2</sub> Single Crystals by Traveling Heater Method. Japanese Journal of Applied Physics, 1990, 29, L1859-L1861.	1.5	20
58	Crystal Orientation Fluctuation of Epitaxial-Lateral-Overgrown GaN with W Mask and SiO <sub>2</sub> Mask Observed by Transmission Electron Diffraction and X-Ray Rocking Curves. Japanese Journal of Applied Physics, 1999, 38, L1299-L1302.	1.5	20
59	TEM analysis of threading dislocations in crack-free Al <sub>x</sub> Ga <sub>1-x</sub> N grown on an AlN(0001) template. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2444-2447.	0.8	20
60	Photoluminescence study of Si-doped a-plane GaN grown by MOVPE. Journal of Crystal Growth, 2009, 311, 2906-2909.	1.5	20
61	Nitridating r-plane sapphire to improve crystal qualities and surface morphologies of a-plane GaN grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2009, 95, .	3.3	20
62	Growth and characterization of Cu <sub>2</sub> ZnSn(S <sub>1-x</sub> Se <sub>x</sub> ) <sub>4</sub> alloys grown by the melting method. Journal of Crystal Growth, 2014, 386, 204-207.	1.5	20
63	Single Crystal Growth of Cu <sub>2</sub> Se Semiconductors by THM. Japanese Journal of Applied Physics, 1993, 32, 156.	1.5	19
64	Transmission Electron Microscopy Characterization of Position-Controlled InN Nanocolumns. Japanese Journal of Applied Physics, 2008, 47, 5330.	1.5	19
65	Extraordinary Optical Transmission Exhibited by Surface Plasmon Polaritons in a Double-Layer Wire Grid Polarizer. Plasmonics, 2015, 10, 1657-1662.	3.4	19
66	Epitaxial growth of CuAlSe <sub>2</sub> on CuGaSe <sub>2</sub> substrates. Journal of Crystal Growth, 1991, 113, 390-394.	1.5	18
67	High Quality GaN Grown by Facet-Controlled ELO (FACELO) Technique. Physica Status Solidi A, 2002, 194, 545-549.	1.7	18
68	Structural and electrical properties of Si-doped a-plane GaN grown on r-plane sapphire by MOVPE. Journal of Crystal Growth, 2009, 311, 2899-2902.	1.5	18
69	Effect of strain on quantum efficiency of InAlN-based solar-blind photodiodes. Applied Physics Letters, 2009, 95, 083504.	3.3	18
70	Impact of face-to-face annealed sputtered AlN on the optical properties of AlGaIn multiple quantum wells. AIP Advances, 2019, 9, 125342.	1.3	18
71	Preparation of CuGaxIn <sub>1-x</sub> S <sub>2</sub> alloys from In solutions. Journal of Crystal Growth, 1993, 134, 174-180.	1.5	17
72	Buried Tungsten Metal Structure Fabricated by Epitaxial-Lateral-Overgrown GaN via Low-Pressure Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2000, 39, L449-L452.	1.5	17

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73	Optical properties of CuGaSe <sub>2</sub> and CuAlSe <sub>2</sub> layers epitaxially grown on Cu(In <sub>0.04</sub> Ga <sub>0.96</sub> )Se <sub>2</sub> substrates. Journal of Applied Physics, 2000, 87, 7294-7302.	2.5	17
74	High temperature growth of AlN film by LP-HVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2252-2255.	0.8	17
75	MOVPE growth of AlN films on nano-patterned sapphire substrates with annealed sputtered AlN. Journal of Crystal Growth, 2020, 532, 125397.	1.5	17
76	Effect of dislocation density on optical gain and internal loss of AlGaIn-based ultraviolet-B band lasers. Applied Physics Express, 2020, 13, 045504.	2.4	17
77	Suppression of Crack Generation Using High-Compressive-Strain AlN/Sapphire Template for Hydride Vapor Phase Epitaxy of Thick AlN Film. Japanese Journal of Applied Physics, 2007, 46, L552-L555.	1.5	16
78	Effects of Substrate Plane on the Growth of High Quality AlN by Hydride Vapor Phase Epitaxy. Applied Physics Express, 2009, 2, 111004.	2.4	16
79	Control of AlN buffer/sapphire substrate interface for AlN growth. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2069-2071.	0.8	16
80	High Crystallinity and Highly Relaxed Al <sub>0.60</sub> Ga <sub>0.40</sub> N Films Using Growth Mode Control Fabricated on a Sputtered AlN Template with High-Temperature Annealing. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900868.	1.8	16
81	High-Quality AlN Template Prepared by Face-to-Face Annealing of Sputtered AlN on Sapphire. Physica Status Solidi (B): Basic Research, 2021, 258, 2000352.	1.5	16
82	Reduction of dislocation density in lattice-relaxed Al <sub>0.68</sub> Ga <sub>0.32</sub> N film grown on periodical 1 $\mu$ m spacing AlN pillar concave-convex patterns and its effect on the performance of UV-B laser diodes. Applied Physics Express, 2022, 15, 031004.	2.4	16
83	Influence of growth interruption and Si doping on the structural and optical properties of Al <sub>x</sub> GaN/AlN (x>0.5) multiple quantum wells. Journal of Crystal Growth, 2007, 298, 500-503.	1.5	15
84	Preparation of high-quality thick AlN layer on nanopatterned sapphire substrates with sputter-deposited annealed AlN film by hydride vapor-phase epitaxy. Japanese Journal of Applied Physics, 2019, 58, SC1003.	1.5	15
85	Distribution Profiles and Annealing Characteristics of Defects in GaAs Induced by Low-Energy FIB Irradiation. Japanese Journal of Applied Physics, 1988, 27, L2037-L2039.	1.5	14
86	Vapor phase epitaxy of CuAlS <sub>2</sub> on CuGaS <sub>2</sub> substrates by the iodine transport method. Journal of Crystal Growth, 1995, 153, 180-183.	1.5	14
87	High performance Schottky UV detectors (265 $\mu$ m) using n-Al <sub>0.5</sub> Ga <sub>0.5</sub> N on AlN epitaxial layer. Physica Status Solidi A, 2003, 200, 151-154.	1.7	14
88	Influence of growth conditions on Al incorporation to Al <sub>x</sub> Ga <sub>1-x</sub> N (x>0.4) grown by MOVPE. Journal of Crystal Growth, 2007, 298, 372-374.	1.5	14
89	Silicon concentration dependence of optical polarization in AlGaIn epitaxial layers. Applied Physics Letters, 2011, 98, .	3.3	14
90	Effects of carrier gas ratio and growth temperature on MOVPE growth of AlN. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 499-502.	0.8	14

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91	Polarity inversion of aluminum nitride by direct wafer bonding. Applied Physics Express, 2018, 11, 031003.	2.4	14
92	Low-threshold-current (~85 mA) of AlGaIn-based UV-B laser diode with refractive-index waveguide structure. Applied Physics Express, 2021, 14, 094009.	2.4	14
93	Fabrication of AlN templates by high-temperature face-to-face annealing for deep UV LEDs. Japanese Journal of Applied Physics, 2021, 60, 120502.	1.5	14
94	Antireflection Effect of Self-Organized GaN Nanotip Structure from Ultraviolet to Visible Region. Japanese Journal of Applied Physics, 2002, 41, L1134-L1136.	1.5	13
95	Mobility enhancement of 2DEG in MOVPE-grown AlGaIn/AlN/GaN HEMT structure using vicinal (0 0 0 1) sapphire. Superlattices and Microstructures, 2009, 46, 812-816.	3.1	13
96	Orientation dependence of polarized Raman spectroscopy for nonpolar, semi-polar, and polar bulk GaN substrates. Applied Physics Letters, 2012, 100, .	3.3	13
97	AlN Grown on a- and n-Plane Sapphire Substrates by Low-Pressure Hydride Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JB31.	1.5	13
98	Using surface-plasmon polariton at the GaP-Au interface in order to detect chemical species in high-refractive-index media. Optics Communications, 2015, 341, 64-68.	2.1	13
99	A design strategy for achieving more than 90% of the overlap integral of electron and hole wavefunctions in high-AlN-mole-fraction Al <sub>x</sub> Ga <sub>1-x</sub> N multiple quantum wells. Applied Physics Express, 2017, 10, 015802.	2.4	13
100	Structural analysis of polarity inversion boundary in sputtered AlN films annealed under high temperatures. Japanese Journal of Applied Physics, 2019, 58, SCCB30.	1.5	13
101	Photoluminescence characteristics of CuAl <sub>x</sub> In <sub>1-x</sub> Se <sub>2</sub> solid solutions grown by iodine transport technique. Journal of Applied Physics, 1992, 72, 3697-3701.	2.5	12
102	Improved quality of CuGaSe <sub>2</sub> and CuAlSe <sub>2</sub> epilayers grown on CuGa <sub>0.96</sub> In <sub>0.04</sub> Se <sub>2</sub> substrates. Applied Physics Letters, 1997, 71, 533-535.	3.3	12
103	Distribution of Threading Dislocations in Epitaxial Lateral Overgrowth GaN by Hydride Vapor-Phase Epitaxy Using Mixed Carrier Gas of H <sub>2</sub> and N <sub>2</sub> . Japanese Journal of Applied Physics, 2002, 41, 75-76.	1.5	12
104	High Quality GaN Grown by Raised-Pressure HVPE. Physica Status Solidi A, 2002, 194, 528-531.	1.7	12
105	Fabrication of AlN templates on SiC substrates by sputtering-deposition and high-temperature annealing. Journal of Crystal Growth, 2019, 510, 13-17.	1.5	12
106	Search for Low-energy Electron Antineutrinos in KamLAND Associated with Gravitational Wave Events. Astrophysical Journal, 2021, 909, 116.	4.5	12
107	Reduction of threading dislocation densities of N-polar face-to-face annealed sputtered AlN on sapphire. Journal of Crystal Growth, 2021, 574, 126309.	1.5	12
108	Reduction of dislocation density in Al <sub>0.6</sub> Ga <sub>0.4</sub> N film grown on sapphire substrates using annealed sputtered AlN templates and its effect on UV-B laser diodes. Journal of Crystal Growth, 2021, 575, 126325.	1.5	12

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109	Solution growth of CuInSe <sub>2</sub> from CuSe solutions. Journal of Crystal Growth, 1995, 156, 404-409.	1.5	11
110	Influence of Ambient Gas on the Epitaxial Lateral Overgrowth of GaN by Metalorganic Vapor Phase Epitaxy. Physica Status Solidi A, 1999, 176, 561-565.	1.7	11
111	Electron Paramagnetic Resonance and Photoluminescence Study of Defects in CuGaSe <sub>2</sub> Single Crystals Grown by the Traveling Heater Method. Japanese Journal of Applied Physics, 2001, 40, 59-63.	1.5	11
112	Field Emission from GaN Self-Organized Nanotips. Japanese Journal of Applied Physics, 2002, 41, L1194-L1196.	1.5	11
113	Photoreflectance of CuAl <sub>x</sub> In <sub>1-x</sub> Se <sub>2</sub> Alloys. Japanese Journal of Applied Physics, 2002, 41, 77-78.	1.5	11
114	Metalorganic Vapor Phase Epitaxy Growth and Study of Stress in AlGa <sub>x</sub> N Using Epitaxial AlN as Underlying Layer. Japanese Journal of Applied Physics, 2003, 42, L572-L574.	1.5	11
115	Deep Electronic Levels of Al <sub>x</sub> Ga <sub>1-x</sub> N with a Wide Range of Al Composition Grown by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2010, 49, 101001.	1.5	11
116	HVPE growth of AlN on trench-patterned 6H-SiC substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 467-469.	0.8	11
117	Growth and characterization of Cu <sub>2</sub> ZnSn(S <sub>1-x</sub> Se <sub>x</sub> ) <sub>4</sub> single crystal grown by traveling heater method. Journal of Crystal Growth, 2015, 423, 9-15.	1.5	11
118	Local and anisotropic strain in AlN film on sapphire observed by Raman scattering spectroscopy. Japanese Journal of Applied Physics, 2019, 58, SCCB17.	1.5	11
119	The nylon balloon for xenon loaded liquid scintillator in KamLAND-Zen 800 neutrinoless double-beta decay search experiment. Journal of Instrumentation, 2021, 16, P08023.	1.2	11
120	Growth of Bulk CuGaS <sub>2</sub> Single Crystals Using Solution Bridgman Method. Japanese Journal of Applied Physics, 1990, 29, L1001-L1003.	1.5	10
121	Fabrication and Optical Characterization of Facet-Controlled ELO (FACELO) GaN by LP-MOVPE. Physica Status Solidi A, 2001, 188, 725-728.	1.7	10
122	Epitaxial lateral overgrowth of GaN on selected-area Si(111) substrate with nitrided Si mask. Journal of Crystal Growth, 2003, 248, 573-577.	1.5	10
123	In-plane structural anisotropy and polarized Raman-active mode studies of nonpolar AlN grown on 6H-SiC by low-pressure hydride vapor phase epitaxy. Journal of Crystal Growth, 2010, 312, 490-494.	1.5	10
124	Cross-sectional X-ray microdiffraction study of a thick AlN film grown on a trench-patterned AlN/Al <sub>2</sub> O <sub>3</sub> template. Journal of Crystal Growth, 2013, 381, 37-42.	1.5	10
125	Crystalline quality improvement of face-to-face annealed MOVPE-grown AlN on vicinal sapphire substrate with sputtered nucleation layer. Journal of Crystal Growth, 2020, 545, 125722.	1.5	10
126	Analysis of carrier injection efficiency of AlGa <sub>x</sub> N UV-B laser diodes based on the relationship between threshold current density and cavity length. Japanese Journal of Applied Physics, 2021, 60, 074002.	1.5	10



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127	Blue emission from InGaN/GaN hexagonal pyramid structures. Superlattices and Microstructures, 2007, 41, 341-346.	3.1	9
128	Optical properties of MOVPE-grown a-plane GaN and AlGaIn. Journal of Crystal Growth, 2009, 311, 2903-2905.	1.5	9
129	Growth of undoped and Zn-doped GaN nanowires. Journal of Crystal Growth, 2009, 311, 2970-2972.	1.5	9
130	Observation of longitudinal-optic-phonon-plasmon-coupled mode in n-type AlGaIn alloy films. Applied Physics Letters, 2011, 99, 251904.	3.3	9
131	Transient photoluminescence of aluminum-rich (Al,Ga)N low-dimensional structures. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 765-768.	1.8	9
132	Solution growth of chalcopyrite compounds single crystal. Renewable Energy, 2015, 79, 127-130.	8.9	9
133	Curvature-controllable and crack-free AlN/sapphire templates fabricated by sputtering and high-temperature annealing. Journal of Crystal Growth, 2019, 512, 131-135.	1.5	9
134	Fabrication of vertical AlGaIn-based deep-ultraviolet light-emitting diodes operating at high current density ( $\sim 443 \text{ kA cm}^{-2}$ ) using a laser liftoff method. Applied Physics Express, 2022, 15, 041006.	2.4	9
135	Centimeter-scale laser lift-off of an AlGaIn UVB laser diode structure grown on nano-patterned AlN. Applied Physics Express, 2022, 15, 051004.	2.4	9
136	Seeded growth of CuGaSe <sub>2</sub> single crystals using the travelling heater method. Journal of Crystal Growth, 1992, 125, 381-383.	1.5	8
137	Growth of CuGaS <sub>2</sub> single crystals by the traveling heater method using CuI solvent. Journal of Crystal Growth, 1994, 144, 236-242.	1.5	8
138	In Situ Monitoring of GaN Reactive Ion Etching by Optical Emission Spectroscopy. Japanese Journal of Applied Physics, 2001, 40, L313-L315.	1.5	8
139	Optical characterization of CuInSe <sub>2</sub> single crystals prepared by travelling heater method. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 2897-2903.	1.8	8
140	Growth of crack-free AlGaIn on selective-area-growth GaN. Journal of Crystal Growth, 2008, 310, 4885-4887.	1.5	8
141	In-plane electric field induced by polarization and lateral photovoltaic effect in a-plane GaN. Applied Physics Letters, 2009, 94, .	3.3	8
142	Fabrication of a binary diffractive lens for controlling the luminous intensity distribution of LED light. Optical Review, 2009, 16, 455-457.	2.0	8
143	a -plane AlN and AlGaIn growth on r -plane sapphire by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2107-2110.	0.8	8
144	HVPE growth of thick AlN on trench-patterned substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1483-1486.	0.8	8

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145	Huge binding energy of localized biexcitons in Al-rich Al <sub>x</sub> Ga <sub>1-x</sub> N ternary alloys. Applied Physics Letters, 2011, 98, 081907.	3.3	8
146	Photoluminescence due to Inelastic Biexciton Scattering from an Al <sub>0.61</sub> Ga <sub>0.39</sub> N Ternary Alloy Epitaxial Layer at Room Temperature. Applied Physics Express, 2012, 5, 072401.	2.4	8
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